

## Two stage Cascade BJT Amplifier

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**Abstract** - Two stage BJT amplifiers for very small signal amplification is presented in this work. With maximum 20V supply voltage and 6mV peak to peak input signal, a fraction of input signal 130uV goes to the first pre amplifier stage and produces an output signal of 11.25V peak to peak at the second stage. The overall gain of the circuit is 86538 times the small signal appearing across the input terminal of the first stage. The design circuit works best for input voltage swing from 100uV peak to peak till 6 mv peak to peak signal voltage. The variation of amplifier gain wrt Vcc is also analyzed. From 7V till 20V if Vcc is varied the gain linearly increases. Maximum gain of 65.24db without output distortion is obtained when the supply voltage is 20V with the least bandwidth. Minimum gain of 31db is obtained with the least 7V voltage supply but having the highest bandwidth. The output noise voltage is from 1.6uV/Hz<sup>1/2</sup> till 270uV/Hz<sup>1/2</sup> as supply voltage increases. The main objective of this work is to optimized and enhanced both gain and bandwidth of the amplifier for very small and low frequency signal amplification.

**Key Words:** emitter follower, voltage divider bias, bypass capacitor, input voltage swing, bandwidth.

### I. INTRODUCTION

A single stage amplifier didn't provide sufficient gain and bandwidth and moreover didn't have matched input and output impedance. To overcome such problems multiple amplifiers are combined for better performance and amplification. Multiple amplifiers are connected in cascade to increase the overall voltage gain of the amplifier. In this type of configuration the output of one amplifier is the input of the next stage as shown in Fig.1. With this arrangement the gain of the amplifier can be increase tremendously [5], [6]. When n numbers of amplifier stages are connected in succession it is called multistage or cascade amplifier. The overall gain of the amplifier is the product of all the gain of each amplifier within the stage which is given by

$$A_v = A_1 * A_2 * \dots * A_n \tag{1}$$

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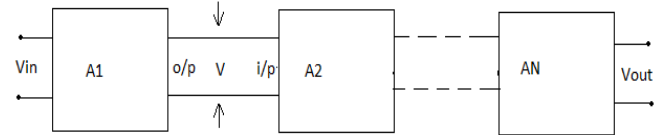


Fig 1. Cascade amplifier

Work on amplifier has already carried out by different researches with different approaches. To increase the overall gain, hybrid combination of BJT-FET-BJT in Triple Darlington topology has already proposed and successfully implemented as high power gain small-signal amplifiers in audio-frequency-range [1]. Two identical JFET in Darlington pair for small signal amplification with wide bandwidth is also carried out. Here variation of gain wrt frequency, biasing resistance, temperature dependency is also presented [2]. Design of high frequency low noise amplifier for wireless communication is also design. BJT is used as LNA to amplify the received RF path with high gain and high sensitivity [3]. Multistage BJT differential power amplifier delivering a power gain of 6db with high efficiency and linearity is also presented [4]. This work is carried on cascade amplifier with two stages having an overall gain of  $A_1 * A_2$  for very small signal amplification in audio frequency range. Between the two stage emitter follower is inserted for impedance matching to deliver maximum power to the preceding stage. Both the two stages are biased in the active mid-point operating region for maximum output swing without distortion [5]. Both AC and DC analysis of the amplifier is also presented. All important parameters of amplifiers like operating point, AC analysis, transient analysis, DC sweep and output noise analysis is also analysed.

### CIRCUIT IMPLEMENTATION AND SIMULATION RESULT

The circuit is implemented with three 2N3904 NPN transistors with passive components listed in Fig. 11. The output of the first stage is directly coupled to emitter follower and finally from the emitter follower it is coupled to the second stage through a coupling capacitor. Bypass capacitor are used to increase the gain of the amplifier [7], [8]. The input signal is fed through a series high resistor which acts as a limiting input of the amplifier to control

the output of the amplifier without distortion. As the input is dividing between the high series input resistance and low internal input impedance of the amplifier only a fraction of input will be amplified initially by the first stage which is built around Q1. Finally the output from the first stage is amplified by the second stage Q2. The emitter follower is inserted in this circuit for impedance matching between the two stages as shown in Fig.2.

Calculated DC operating values	Simulation results
ICQ = 1.66mA	ICQ = 1.74mA
Vce = 10.04 V	Vce =9.59V
Vbb = 2.36V	Vbb =2.34V
Vc = 11.7V	Vc = 11.27v
Ve= 1.66V	Ve=1.68V

Fig. 4 comparison of results

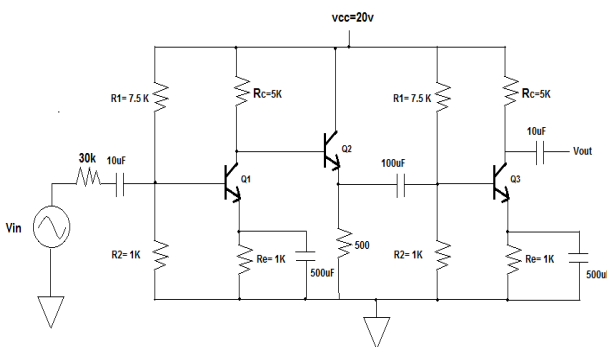


Fig. 2 Two-stage small signal amplifier

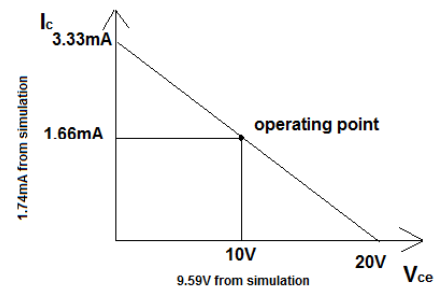


Fig 5. DC load line and operating point of Q1

DC analysis: The DC equivalent circuit of the amplifier stage is obtained by opening all capacitor and shorting all input source as shown in Fig.3. The transistor follows voltage divider biasing method [5]. Biasing resistances are designed to make the transistor operate in the active region. All the calculated values of the operating point of the transistor along with the simulation results are shown in Fig. 4.

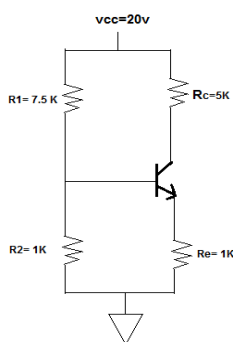


Fig.3 DC equivalent circuit

The transistor is biased in the active region for maximum gain undistorted output as shown in the DC load line in Fig. 5. The current gain  $\beta$  of the device is 337. The output of the first stage is directly coupled to the emitter follower eliminating the need of biasing resistor for the emitter follower. The collector voltage of Q1 is used to bias the emitter follower which has a gain slightly less than 1. The operating point of emitter follower is shown in Fig.6.

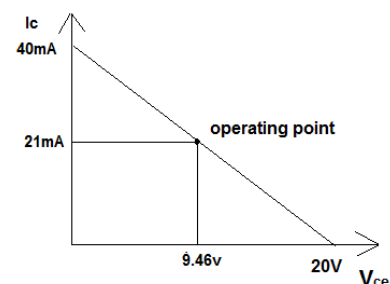


Fig 6. DC load line and operating point of Q2

AC Analysis: AC equivalent circuit is obtained by shorting all capacitor and grounding the DC supply voltage and replacing the transistor with T model as shown in Fig. 7

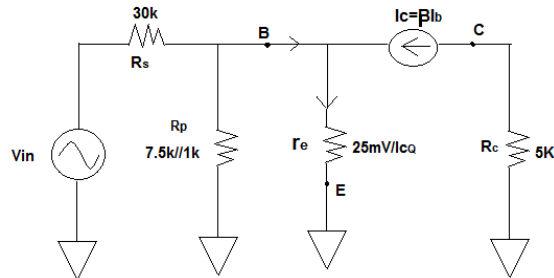


Fig.7 AC equivalent circuit

The gain of the amplifier is the ratio of output to input

$$A_v = (o/p \text{ vol}) / (i/p \text{ vol}) \tag{2}$$

o/p vol is the total output voltage seen across  $R_c$  and the i/p vol is the voltage seen across the base emitter resistor  $r_e$  having a magnitude of  $25mV/I_c$ . Therefore the gain of the amplifier can be express as

$$A_v = (-5k \cdot I_c) / (r_e \cdot I_e)$$

$$A_v = -5k/r_e \text{ since } I_c \sim I_e \tag{3}$$

The input impedance  $Z_i$  of the circuit is given by

$$Z_i = R_p // (\beta + 1)r_e \tag{4}$$

And the amplifier output impedance  $Z_o$  is express as

$$Z_o = R_c \tag{5}$$

Based on these three parameters i.e gain, input impedance and output impedance the overall amplifier circuit representation is shown in Fig.8

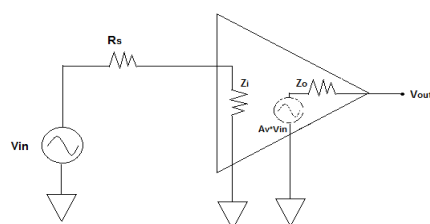


Fig. 8 General amplifier equivalent circuit

The negative sign in the gain expression indicates the input and output are out of phase by 180°. The gain in db and bandwidth of the amplifier as a function of supply voltage with 6mv peak to peak input signal is shown in Fig. 9

Supply voltage Vcc	Gain in db	bandwidth
7v	31db	5hz-1.5Mhz
9v	43.30db	7hz-1Mhz
11v	50.20db	10hz-750Khz
13v	55.06db	13hz-614Khz
15v	58.93db	17hz-503Khz
17v	61.75db	19hz-447Khz
19v	64.23	21hz-450Khz
20v	65.24db	23hz-400Khz

Fig.9 variation of gain and BW wrt Vcc

The circuit work best from 7V to 20V Vcc. Gain of the amplifier as a function of Vcc is shown on Fig.10.

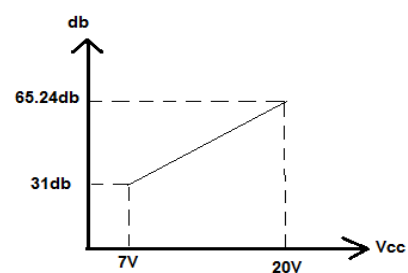


Fig.10 Graphical interpretation of Vcc Vs gain

The minimum voltage supply required is 6V with a gain of 20db. Below 6V there is no amplification. Above 20V the gain increases but the output becomes distorted and clip off. The circuit will perform best between 7V to 20 V with faithful output. The bandwidth on the other hand is limited with the increase in Vcc. When Vcc is 20V bandwidth is from 23Hz-400 KHz which is the least but having the maximum gain.

The amplifier circuit consists of three 2N3904 transistor as shown in Fig.1. The first and the last stage follow the same biasing technique i.e voltage divider and in between the two stages, emitter follower is inserted to provide a good overall voltage gain and for proper impedance matching between the two stages. This reduces the attenuation due to inter-stage loading. Both the stages i.e first stage and the output stage is bias in the active region for maximum signal swing without clipping. Full amplification is obtained in the second stage which swings around ground reference voltage. Circuit elements for the propose amplifier is listed below in the component table.

List of components

components	quantity
2N3904 transistor	3
500 uF bypass capacitor	1
500 uF bypass capacitor	1
100uF coupling capacitor	1
10uF coupling capacitor	2
9KΩ resistor	2
500Ω	1
5 kΩ resistor	2
1k Ω	4
33KΩ	1

Fig.11 circuit component list

The AC simulation is carried out with input voltage of 6mV p-p and supply voltage of 20V. It has a constant gain of 65.24db within the bandwidth and after 400 KHz it roll off as shown in the simulation result in Fig. 12

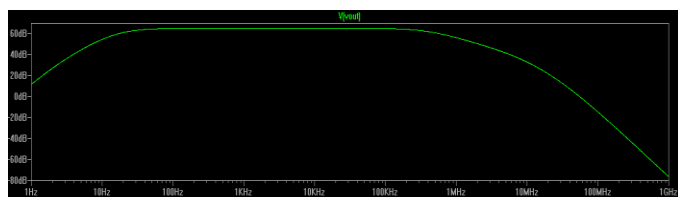


Fig.12 AC signal simulation result

With the same input condition and supply voltage, transient analysis and output noise analysis is carried out as shown in Fig 13 & 14. From the

simulation result the amplified output voltage swing is 11.25V peak to peak and the noise is 270uV/Hz<sup>1/2</sup>.

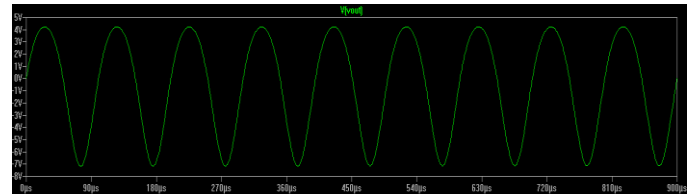


Fig.13 transient analysis of output

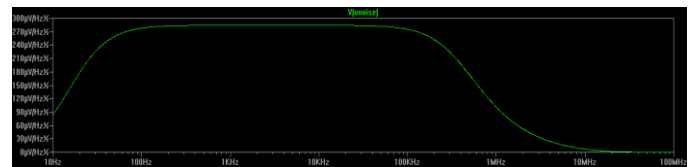


Fig.14. output noise analysis

The effect of DC sweep supply voltage wrt I<sub>CO</sub> and I<sub>EO</sub> is also analyzed as shown in Fig.15. Both the operating current which is almost equal linearly rises from 0.2mA to 1.74mA from the simulation result

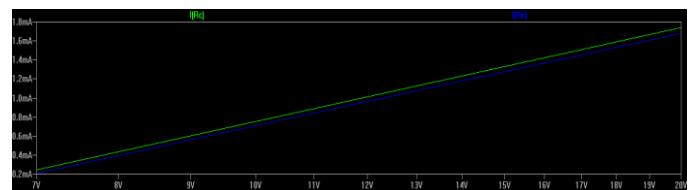


Fig.15 DC sweep simulation result

### 3. CONCLUSIONS

Maximum gain of 65.24db faithful output is obtained with supply voltage of 20V. When voltage is increase beyond 20V the gain increases but the output is clipped off. The gain and bandwidth of the amplifier is optimized precisely with all the biasing circuit elements. The maximum allowable input swing is 6mV peak to peak. To control the overall gain of the amplifier variable load 100K can be connected at the output stage. All the simulation result is also shown in the simulation result. Tool used for simulation is LT SpiceIV.

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## BIOGRAPHIES



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